## **DSC8Q01**

## Silicon NPN epitaxial planar type darlington

For low frequency output amplification
Darlington connection
DSC7Q01 in MT-2 through hole type package

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub> with excellent linearity
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

#### Packaging

Radial type: 2000 pcs / carton

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	100	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	80	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V
Collector current	$I_{C}$	1	A
Peak collector current	I <sub>CP</sub>	1.5	A
Collector power dissipation	P <sub>C</sub>	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Note) Printed circuit board: Copper foil area of 1  $\rm cm^2$  or more, and the board thickness of 1.7 mm for the collector portion

Absolute maximum rating without heat sink for P<sub>C</sub> is 0.5 W

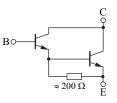
### ■ Package

• Code

MT-2-A2-B

- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

#### ■ Marking Symbol: 5K



### ■ Electrical Characteristics $T_a = 25$ °C±3°C

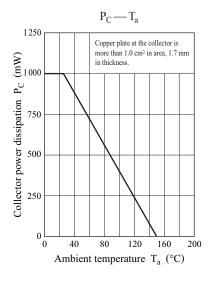
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 100  \mu A, I_E = 0$	100			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_{E} = 0$			0.1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_{C} = 0$			0.1	μΑ
Forward current transfer ratio *1, 2	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}$	4000		40 000	_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = 1  \text{A}, I_{\rm B} = 1  \text{mA}$			1.8	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			2.2	V

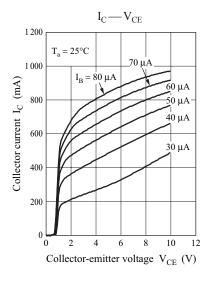
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

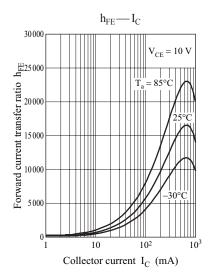
- 2. \*1: Pulse measurement
  - \*2: Rank classification

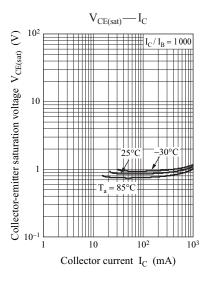
Code	Q	R	S
Rank	Q	R	S
$h_{\mathrm{FE}}$	4000 to 10000	8000 to 20000	16000 to 40000
Marking Symbol	5KQ	5KR	5KS

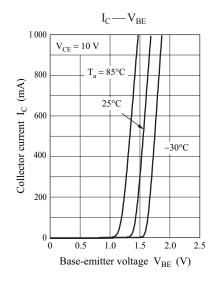
DSC8Q01 Panasonic

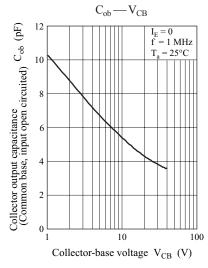


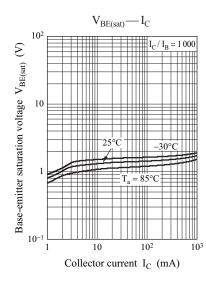








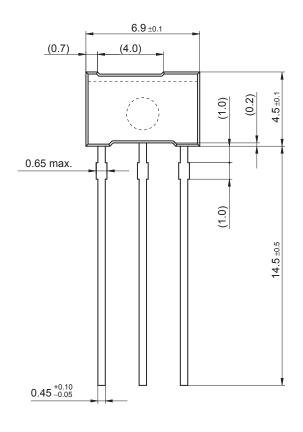


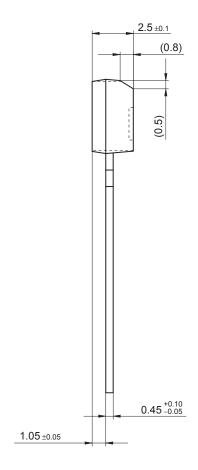


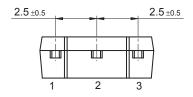
2 Ver. AED

Panasonic DSC8Q01

MT-2-A2-B Unit: mm







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